## 2SD1845

### Silicon NPN Triple-Diffused Planar Type

#### Horizontal Deflection Output

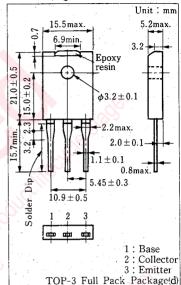
#### **■** Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

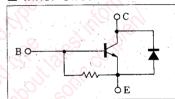
#### ■ Absolute Maximum Ratings (Tc=25°C)

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Item	Symbol	Value	Unit	
Collector-base voltage	$V_{CBO}$	1500	v	
C. II.	V <sub>CES</sub>	1500	V	
Collector-emitter voltage	V <sub>CEO</sub>	700	V	
Emitter-base voltage	$V_{\mathrm{EBO}}$	7	V	
Peak collector current	I <sub>CP</sub>	7	A	
Collector current	I <sub>C</sub>	2.5	(A)	
Base current	$I_{\mathrm{B}}$	1.5	A	
Collector power T <sub>C</sub> =25°C	P <sub>C</sub>	60	W	
dissipation $T_a = 25^{\circ}C$		3	W	
Junction temperature	$T_{j}$	150	°C '	
Storage temperature	$T_{\text{stg}}$	-55~+150	0 ℃	

#### ■ Package Dimensions

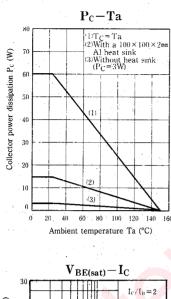


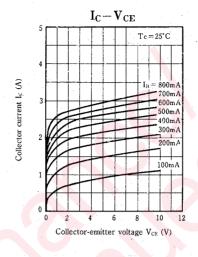
#### ■ Inner Circuit

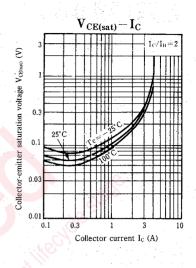


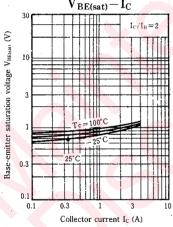
#### ■ Electrical Characteristics (Tc=25°C)

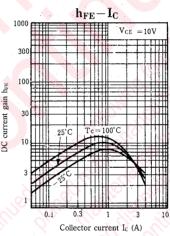
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	Ісво	$V_{CB} = 750V, I_{E} = 0$	Ψ	S 4 1 5	10	μΑ
		$V_{\rm CB} = 1500  \text{V},  I_{\rm E} = 0$			1	mA
Emitter-base voltage	V <sub>EBO</sub>	$I_{\rm E} = 500  \rm mA, \ I_{\rm C} = 0$	7			V
DC current gain	h <sub>FE</sub>	$V_{CE} = 5V, I_{C} = 0.5A$	5		25	
		$V_{CE} = 10V, I_{C} = 2A$	3.5		1 1	·
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	$I_C = 2A, I_B = 0.6A$			8	V
Base-emitter saturation voltage	V <sub>BE (sat)</sub>	$I_{\rm C} = 2A, I_{\rm B} = 0.6A$			1.5	·V
Transition frequency	$f_{T}$	$V_{CE} = 10V, I_{C} = 0.5A, f = 0.5MHz$		2		MHz
Storage time (L load)	$t_{\rm stg}$	$I_C = 2A$ , $I_{B1} = 0.6A$			, 7	μs
Collector current fall time (L load)	tf	$I_{B2} = -0.6A, L_{leak} = 5\mu H$			0.8	μs
Storage time (R load)	t <sub>stg</sub>	$I_C = 2A, I_{B1} = 0.6A$	1	1.5		μs
Collector current fall time (R load)	t <sub>f</sub>	$I_{B2} = -1.2A$ , $V_{CC} = 200V$		0.2		μs
Diode forward voltage	V <sub>F</sub>	$I_{\rm C} = -2.5  \text{A}, \ I_{\rm B} = 0$			2	. V_

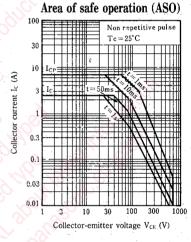


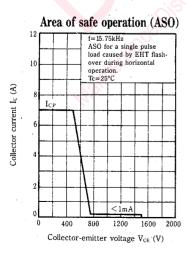


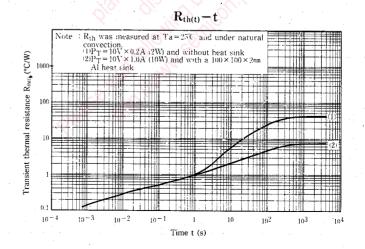












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